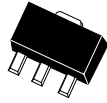


**CXT2222A**  
**SURFACE MOUNT**  
**NPN SILICON TRANSISTOR**



**SOT-89 CASE**

# Central<sup>TM</sup>

**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CXT2222A type is an NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for small signal general purpose and switching applications.

**MAXIMUM RATINGS** ( $T_A=25^{\circ}\text{C}$ )

	<b>SYMBOL</b>		<b>UNITS</b>
Collector-Base Voltage	$V_{CBO}$	75	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	$I_C$	600	mA
Power Dissipation	$P_D$	1.2	W
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	$\theta_{JA}$	104	$^{\circ}\text{C/W}$

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

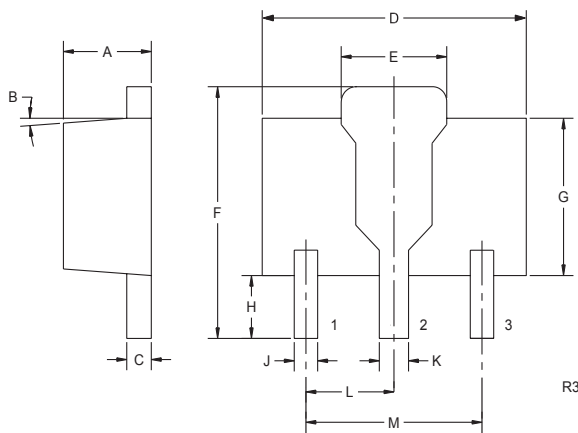
<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>
$I_{CBO}$	$V_{CB}=60\text{V}$		10	nA
$I_{CBO}$	$V_{CB}=60\text{V}, T_A=125^{\circ}\text{C}$		10	$\mu\text{A}$
$I_{EBO}$	$V_{EB}=3.0\text{V}$		10	nA
$I_{CEV}$	$V_{CE}=60\text{V}, V_{EB}=3.0\text{V}$		10	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	75		V
$BV_{CEO}$	$I_C=10\text{mA}$	40		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	6.0		V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$		0.3	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		1.0	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	0.6	1.2	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		2.0	V
$h_{FE}$	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	35		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	50		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	75		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100	300	
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=150\text{mA}$	50		
$h_{FE}$	$V_{CE}=10\text{V}, I_C=500\text{mA}$	40		
$f_T$	$V_{CE}=20\text{V}, I_C=20\text{mA}, f=100\text{MHz}$	300		MHz
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		8.0	pF
$C_{ib}$	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		25	pF

**SURFACE MOUNT  
NPN SILICON TRANSISTOR**

**ELECTRICAL CHARACTERISTICS** (Continued)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$h_{ie}$	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	2.0	8.0	$k\Omega$
$h_{ie}$	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	0.25	1.25	$k\Omega$
$h_{re}$	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$		8.0	$\times 10^{-4}$
$h_{re}$	$V_{CE}=10V, I_C=10mA, f=1.0kHz$		4.0	$\times 10^{-4}$
$h_{fe}$	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	50	300	
$h_{fe}$	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	75	375	
$h_{oe}$	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	5.0	35	$\mu mhos$
$h_{oe}$	$V_{CE}=10V, I_C=10mA, f=1.0kHz$	25	200	$\mu mhos$
$r_b' C_c$	$V_{CB}=10V, I_E=20mA, f=31.8MHz$		150	ps
NF	$V_{CE}=10V, I_C=100\mu A, R_S=1.0k\Omega, f=1.0kHz$		4.0	dB
$t_d$	$V_{CC}=30V, V_{BE}=0.5, I_C=150mA, I_{B1}=15mA$		10	ns
$t_r$	$V_{CC}=30V, V_{BE}=0.5, I_C=150mA, I_{B1}=15mA$		25	ns
$t_s$	$V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA$		225	ns
$t_f$	$V_{CC}=30V, I_C=150mA, I_{B1}=I_{B2}=15mA$		60	ns

**SOT-89 CASE - MECHANICAL OUTLINE**



BOTTOM VIEW

**LEAD CODE:**

- 1) EMITTER
- 2) COLLECTOR
- 3) BASE

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.067	1.40	1.70
B	4°		4°	
C	0.016	0.018	0.40	0.46
D	0.173	0.185	4.40	4.70
E	0.070	0.074	1.79	1.87
F	0.146	0.177	3.70	4.50
G	0.094	0.106	2.40	2.70
H	0.028	0.051	0.70	1.30
J	0.015	0.019	0.38	0.48
K	0.019	0.023	0.48	0.58
L	0.059		1.50	
M	0.118		3.00	

SOT-89 (REV: R3)